



Express Mail No. EV 346 811 082 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No. 2491

Application No.: 10/784,017

Group Art Unit:

Filing Date: February 20, 2004

Examiner:

For: METHOD FOR FORMING A RELAXED OR  
PSEUDO-RELAXED USEFUL LAYER ON A  
SUBSTRATE

Atty. Docket No.: 4717-10200

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of (8) references for the Examiner's review and consideration. These references were cited in the specification of the application and in preliminary search report and a copy is enclosed..

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee or certification is believed to be due for this submission since the references are being submitted concurrent with the filing of this application. Should any fees be required, however, please charge such fees to **Winston & Strawn Deposit Account No. 50-1814.**

Date: 6/1/04

Respectfully submitted,

  
Allan A. Fanucci (Reg. No. 30,256)

**WINSTON & STRAWN LLP**  
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Enclosures

NY:868044.1



<b>LIST OF REFERENCES CITED BY APPLICANT</b> <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.:	APPLICATION NO.:
	4717-10200	10/784,017
	APPLICANT:	
	Bruno GHYSELEN et al.	
FILING DATE:	GROUP:	
February 20, 2004		

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA		5,461,243	10/1995	Ek et al.	257	190	
AB		6,352,942 B1	3/2002	Luan et al.	438	770	
AC		2002/0072130	6/2002	Cheng et al.	438	10	
AD							
AE							
AF							
AG							
A1							

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ							
	AK							
	AL							

**OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)**

AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si <sub>x</sub> Ge <sub>y</sub> /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
AN	K.D. Hobart et al. "Compliant Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7 , pp. 897-900 (2000)
AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997)
AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

EXAMINER	DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.